

1. General description

Trench Maximum Efficiency General Application (MEGA) Schottky barrier rectifier, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \le 15 A$
- Reverse voltage: V_R ≤ 45 V
- Low forward voltage
- Low leakage current due to Trench MEGA Schottky technology
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 120 °C; square wave	-	-	15	A		
V _R	reverse voltage	T _j = 25 °C	-	-	45	V		
V _F	forward voltage	$\label{eq:last} \begin{array}{l} I_F = 15 \; A; \; t_p \leq 300 \; \mu s; \; \overline{o} \leq 0.02 \; \; ; \\ T_j = 25 \; ^\circ C; \; pulsed \end{array}$	-	480	580	mV		
I _R	reverse current	$V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03 ;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	16	50	μA		
		$V_R = 45 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.03 ;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	30	100	μA		





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		
2	А	anode		
3	К	cathode	2 CFP15 (SOT1289)	

6. Ordering information

Table 3. Ordering information							
Type number	Package	ackage					
	Name	Description	Version				
PMEG45T15EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG45T15EPD	4515 TTTT

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Limiting values 8.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _R	reverse voltage	T _j = 25 °C		-	45	V
I _F	forward current	T _{sp} = 115 °C; δ = 1		-	21	А
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 120 °C; square wave		-	15	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	210	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.4	W
			[2]	-	1.8	W
			[3]	-	3.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint. [3]

Thermal characteristics 9.

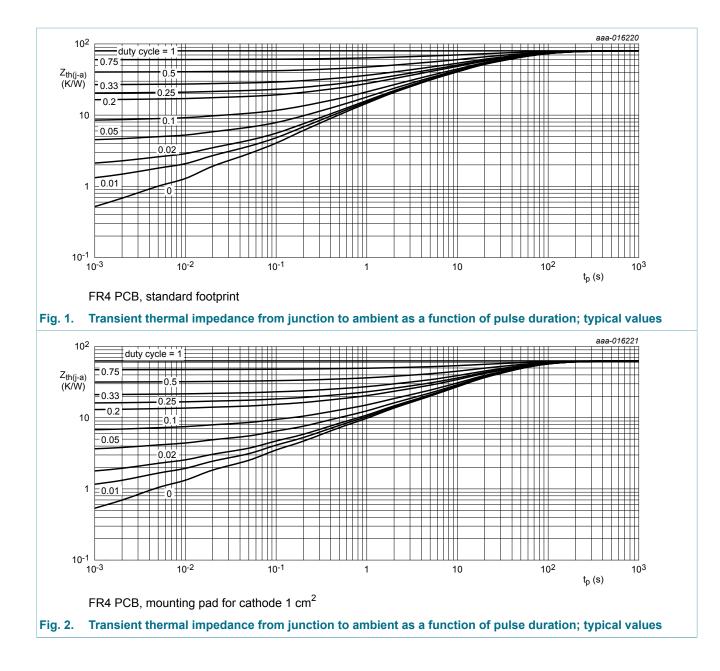
Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui()-a)	thermal resistance	in free air	[1][2]	-	-	90	K/W
	from junction to		[1][3]	-	-	70	K/W
	ampient		[1][4]	-	-	40	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	3	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [2]
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.
- [5] Soldering point of cathode tab.

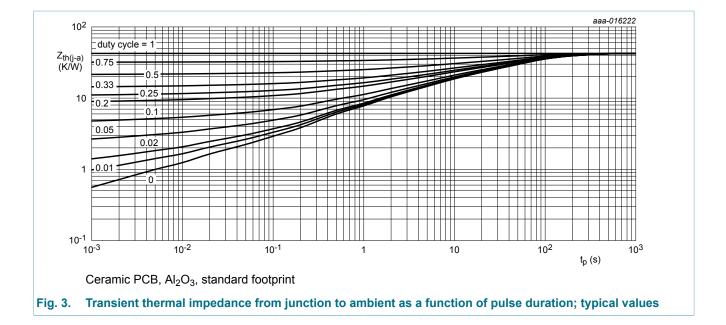
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)R}	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; t_p ≤ 1.2 ms; δ ≤ 0.12; pulsed	45	-	-	V
V _F	forward voltage	$\begin{split} I_F = 1 \text{ A}; t_p \leq 300 \; \mu s; \delta \leq 0.02 \; \; ; \\ T_j = 25 \; ^\circ\text{C}; \text{pulsed} \end{split}$	-	320	380	mV
		$\begin{split} I_{\text{F}} &= 5 \text{ A}; t_{\text{p}} \leq 300 \; \mu\text{s}; \delta \leq 0.02 \; \; ; \\ T_{\text{j}} &= 25 \; ^{\circ}\text{C}; \; \text{pulsed} \end{split}$	-	390	460	mV
		I _F = 10 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C; pulsed	-	440	-	mV
	I _F = 15 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C; pulsed	-	480	580	mV	
		$I_F = 15 \text{ A}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ; \\ T_j = 125 ^\circ\text{C}; \text{ pulsed}$	-	405 -	-	mV
R	reverse current	V_R = 5 V; $t_p \le 3$ ms; $\delta \le 0.03$; T _j = 25 °C; pulsed	-	12	-	μA
		V_R = 10 V; $t_p \le 3$ ms; $\delta \le 0.03$; T _j = 25 °C; pulsed	-	16	50	μA
		V_R = 45 V; $t_p \le 3$ ms; $\delta \le 0.03$; T _j = 25 °C; pulsed	-	30	100	μA
		V_R = 45 V; $t_p \le 3$ ms; $\delta \le 0.03$; T _j = 125 °C; pulsed	-	22	-	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _i = 25 °C	_	2200	_	pF

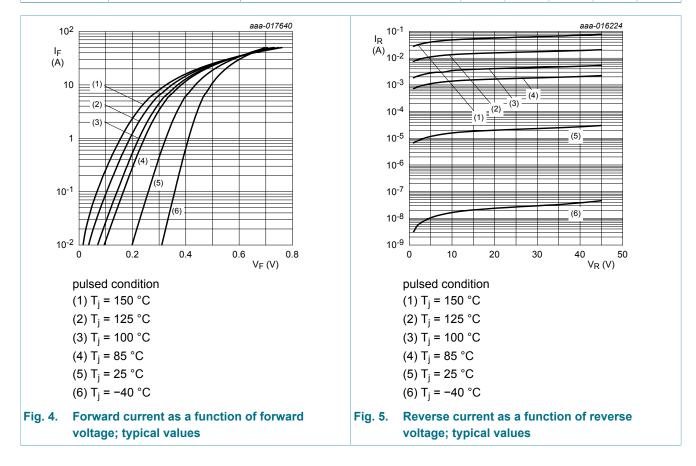
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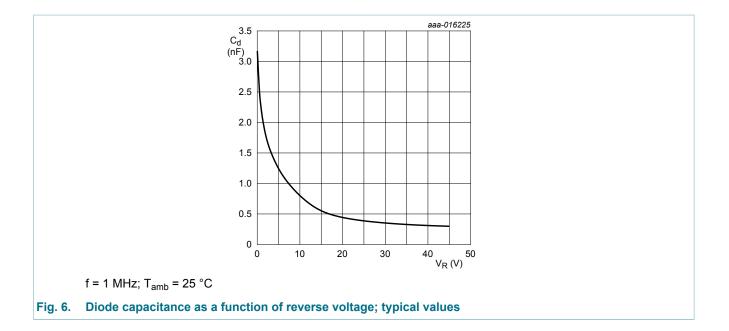
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		V_R = 10 V; f = 1 MHz; T _j = 25 °C	-	800	-	pF
t _{rr}	reverse recovery time step recovery	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	60	-	ns
t _{rr}	reverse recovery time ramp recovery	dI _F /dt = 200 A/µs; T _j = 25 °C; I _F = 6 A; V _R = 26 V	-	20	-	ns
V _{FRM}	peak forward recovery voltage	I _F = 0.5 A; dI _F /dt = 20 A/μs; T _j = 25 °C	-	305	-	mV

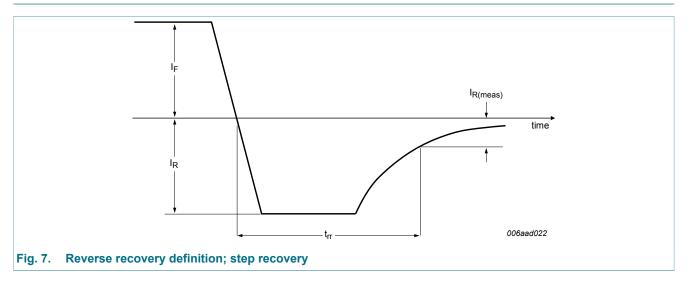


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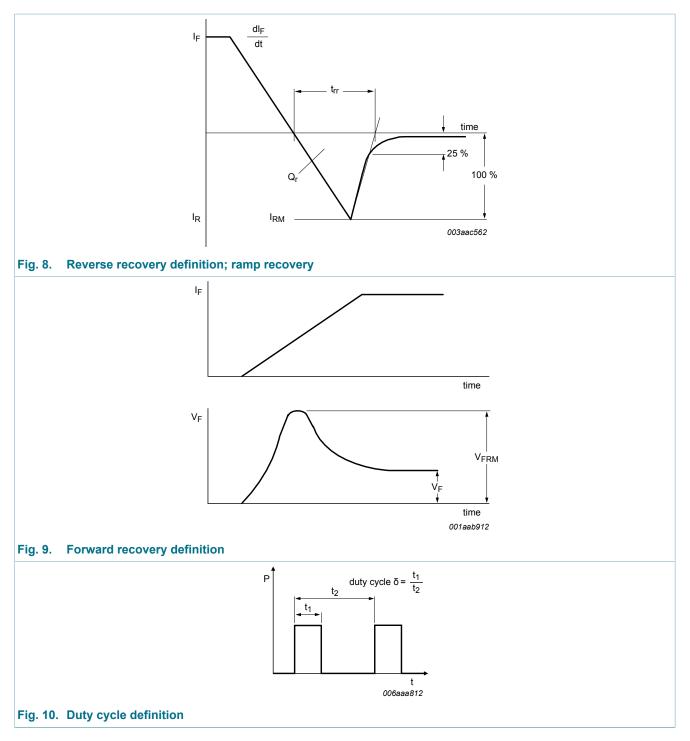


11. Test information



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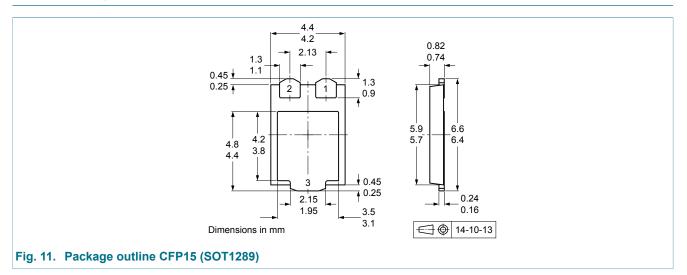
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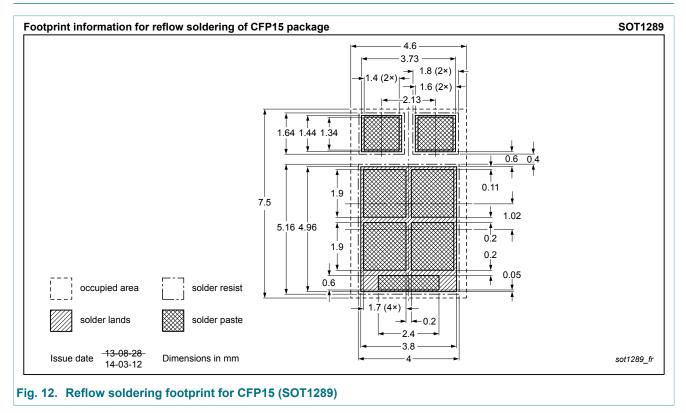
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG45T15EPD v.3	20150904	Product data sheet	-	PMEG45T15EPD v.2			
Modifications:	Editorial edit in cone						
PMEG45T15EPD v.2	20150629	Product data sheet	-	PMEG45T15EPD v.1			
PMEG45T15EPD v.1	20150330	Objective data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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